

REMARKS

By this amendment, claims 56 and 66 have been amended. Claims 56-70 are pending in the application. Applicants reserve the right to pursue the original claims and other claims in this and other applications.

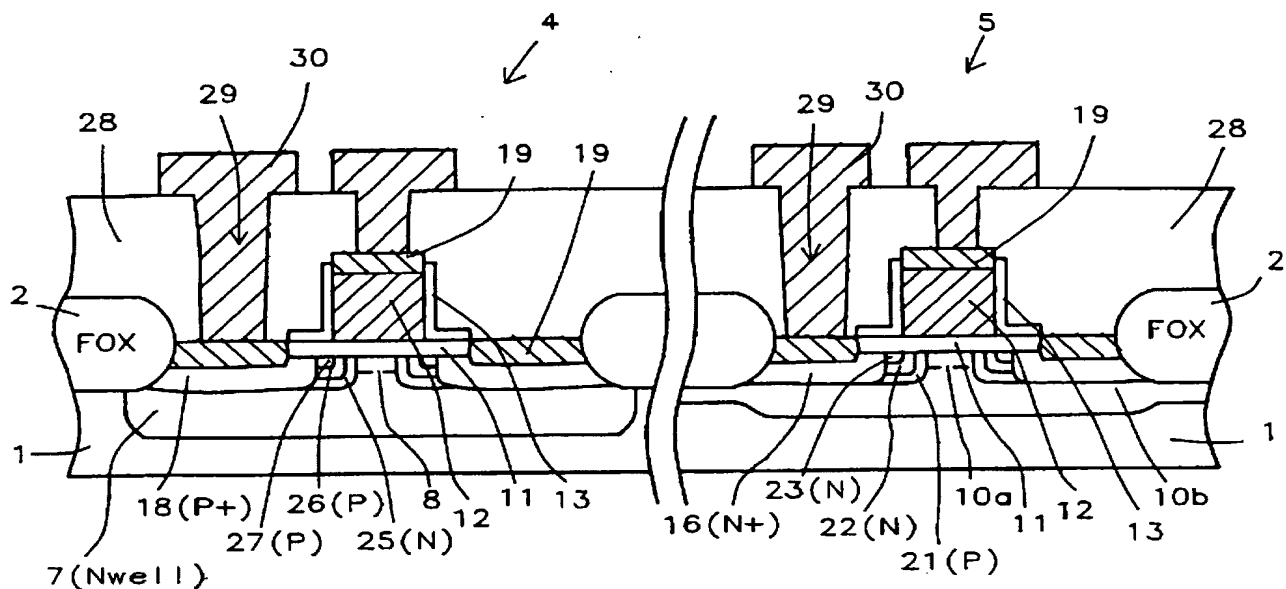
Claims 56-70 stand rejected under 35 U.S.C. 102(b) as being anticipated by Tsai et al. (US 5,757,045). This rejection is respectfully traversed.

Claim 56 recites, *inter alia*, an integrated circuit comprising “a gate structure having sidewalls ...; a plurality of first diffusion regions implanted with a first dopant ...; a plurality of second diffusion regions implanted with a second dopant, said plurality of second diffusion regions each being adjacent to the sidewalls of said gate structure; wherein each of said first diffusion regions is associated with and located beneath and adjacent to a respective second diffusion region ...; and none of said plurality of second diffusion regions include any portion which extends beneath said gate structure” (emphasis added). Claim 66 recites a semiconductor device comprising, *inter alia*, “a gate structure ... having a thermally reoxidized sidewall ...; and a plurality of diffusion regions, each of said diffusion regions being formed adjacent to the thermally reoxidized sidewall; wherein each of said diffusion regions respectively comprise first and second portions respectively having first and second dopant concentrations ...; none of said second portion is located underneath said interior surface of said thermally reoxidized sidewall, and each of said first portions is associated with and located beneath and adjacent to a respective associated second portion” (emphasis added). Tsai et al. does not disclose these limitations.

Tsai et al. discloses in FIG. 13 p-type region 21, and n-type regions 22, 23, and 16. N-type region 22 extends below the gate structure. N-type region 23 does not extend below the gate, but it is also not adjacent to a p-type region, such as p-type

region 21. N-type region 16 does not extend below the gate, but it also is not located adjacent to the sidewall of gate structure 12. Tsai et al. FIG. 13 (reproduced below). There is no first diffusion region associated with and located beneath and adjacent to respective second diffusion region as recited in claims 56 and 66. The doped regions are not located adjacent to the sidewall of the gate structure. Since Tsai et al. does not disclose all the limitations of claims 56 and 66, claims 56 and 66 are not anticipated by Tsai et al. Claims 57-65 depend from claim 56 and are patentable at least for the reasons mentioned above. Claims 67-70 depend from claim 66 and are patentable at least for the reasons mentioned above. Applicants respectfully request that the 35 U.S.C. § 102(b) rejection of claims 56-70 be withdrawn.

Tsai et al. FIG. 13



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In view of the above amendment, Applicant believes the pending application is in condition for allowance.

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Respectfully submitted,

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